

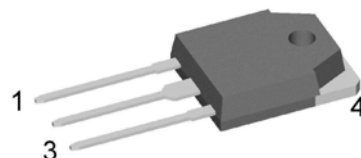
# HiPerFRED<sup>2</sup>

$$\begin{aligned} V_{RRM} &= 300\text{ V} \\ I_{FAV} &= 2 \times 60\text{ A} \\ t_{rr} &= 35\text{ ns} \end{aligned}$$

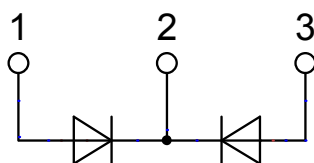
High Performance Fast Recovery Diode  
Low Loss and Soft Recovery  
Common Cathode

Part number

**DPG120C300QB**



Backside: cathode



## Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very short recovery time
- Improved thermal behaviour
- Very low  $I_{rm}$ -values
- Very soft recovery behaviour
- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low  $I_{rm}$  reduces:
  - Power dissipation within the diode
  - Turn-on loss in the commutating switch

## Applications:

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode
- Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

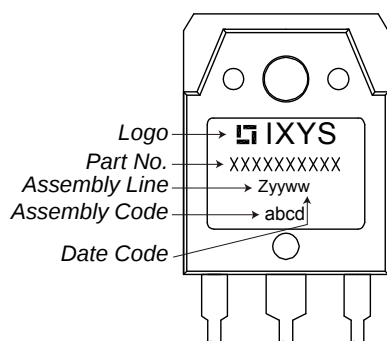
## Package: TO-3P

- Industry standard outline compatible with TO-247
- RoHS compliant
- Epoxy meets UL 94V-0

| Fast Diode        |                                              |                                                                                    |                         | Ratings                 |      |      |      |  |
|-------------------|----------------------------------------------|------------------------------------------------------------------------------------|-------------------------|-------------------------|------|------|------|--|
| Symbol            | Definition                                   | Conditions                                                                         |                         | min.                    | typ. | max. | Unit |  |
| V <sub>RSM</sub>  | max. non-repetitive reverse blocking voltage | T <sub>VJ</sub> = 25°C                                                             |                         |                         |      | 300  | V    |  |
| V <sub>RRM</sub>  | max. repetitive reverse blocking voltage     | T <sub>VJ</sub> = 25°C                                                             |                         |                         |      | 300  | V    |  |
| I <sub>R</sub>    | reverse current, drain current               | V <sub>R</sub> = 300 V                                                             | T <sub>VJ</sub> = 25°C  |                         |      | 1    | μA   |  |
|                   |                                              | V <sub>R</sub> = 300 V                                                             | T <sub>VJ</sub> = 150°C |                         |      | 0.35 | mA   |  |
| V <sub>F</sub>    | forward voltage drop                         | I <sub>F</sub> = 60 A                                                              | T <sub>VJ</sub> = 25°C  |                         |      | 1.40 | V    |  |
|                   |                                              | I <sub>F</sub> = 120 A                                                             |                         |                         |      | 1.72 | V    |  |
|                   |                                              | I <sub>F</sub> = 60 A                                                              | T <sub>VJ</sub> = 125°C |                         |      | 1.10 | V    |  |
|                   |                                              | I <sub>F</sub> = 120 A                                                             |                         |                         |      | 1.45 | V    |  |
| I <sub>FAV</sub>  | average forward current                      | T <sub>C</sub> = 130°C                                                             | T <sub>VJ</sub> = 175°C |                         |      | 60   | A    |  |
|                   |                                              | rectangular      d = 0.5                                                           |                         |                         |      |      |      |  |
| V <sub>F0</sub>   | threshold voltage                            | } for power loss calculation only                                                  |                         |                         |      | 0.69 | V    |  |
| r <sub>F</sub>    | slope resistance                             |                                                                                    |                         |                         |      | 5.8  | mΩ   |  |
| R <sub>thJC</sub> | thermal resistance junction to case          |                                                                                    |                         |                         |      | 0.55 | K/W  |  |
| R <sub>thCH</sub> | thermal resistance case to heatsink          |                                                                                    |                         |                         | 0.25 |      | K/W  |  |
| P <sub>tot</sub>  | total power dissipation                      | T <sub>C</sub> = 25°C                                                              |                         |                         |      | 275  | W    |  |
| I <sub>FSM</sub>  | max. forward surge current                   | t = 10 ms; (50 Hz), sine; V <sub>R</sub> = 0 V                                     |                         | T <sub>VJ</sub> = 45°C  |      | 450  | A    |  |
| C <sub>J</sub>    | junction capacitance                         | V <sub>R</sub> = 150 V   f = 1 MHz                                                 |                         | T <sub>VJ</sub> = 25°C  | 80   |      | pF   |  |
| I <sub>RM</sub>   | max. reverse recovery current                | } I <sub>F</sub> = 60 A; V <sub>R</sub> = 200 V<br>-di <sub>F</sub> /dt = 200 A/μs |                         | T <sub>VJ</sub> = 25°C  | 3.5  |      | A    |  |
|                   |                                              |                                                                                    |                         | T <sub>VJ</sub> = 125°C | 9    |      | A    |  |
| t <sub>rr</sub>   | reverse recovery time                        |                                                                                    |                         | T <sub>VJ</sub> = 25°C  | 35   |      | ns   |  |
|                   |                                              |                                                                                    |                         | T <sub>VJ</sub> = 125°C | 65   |      | ns   |  |

| Package TO-3P |                              |                            | Ratings |      |      |      |
|---------------|------------------------------|----------------------------|---------|------|------|------|
| Symbol        | Definition                   | Conditions                 | min.    | typ. | max. | Unit |
| $I_{RMS}$     | RMS current                  | per terminal <sup>1)</sup> |         |      | 70   | A    |
| $T_{VJ}$      | virtual junction temperature |                            | -55     |      | 175  | °C   |
| $T_{op}$      | operation temperature        |                            | -55     |      | 150  | °C   |
| $T_{stg}$     | storage temperature          |                            | -55     |      | 150  | °C   |
| Weight        |                              |                            |         | 5    |      | g    |
| $M_D$         | mounting torque              |                            | 0.8     |      | 1.2  | Nm   |
| $F_C$         | mounting force with clip     |                            | 20      |      | 120  | N    |

## Product Marking



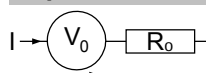
## Part number

D = Diode  
 P = HiPerFRED  
 G = extreme fast  
 120 = Current Rating [A]  
 C = Common Cathode  
 300 = Reverse Voltage [V]  
 QB = TO-3P (3)

| Ordering | Part Number  | Marking on Product | Delivery Mode | Quantity | Code No. |
|----------|--------------|--------------------|---------------|----------|----------|
| Standard | DPG120C300QB | DPG120C300QB       | Tube          | 30       | 503821   |

## Equivalent Circuits for Simulation

\* on die level

 $T_{VJ} = 175^{\circ}\text{C}$ 

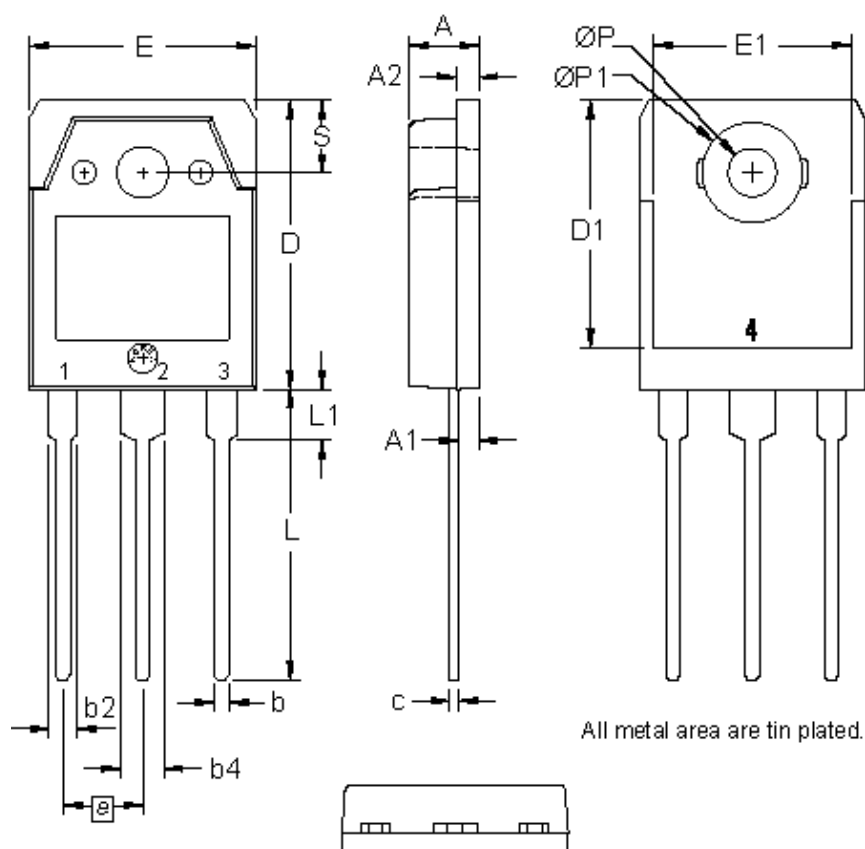
Fast Diode

 $V_{0\max}$  threshold voltage 0.69

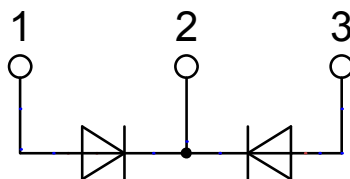
V

 $R_{0\max}$  slope resistance \* 3.2

mΩ

**Outlines TO-3P**


| Dim. | Millimeter |       | Inches    |       |
|------|------------|-------|-----------|-------|
|      | min        | max   | min       | max   |
| A    | 4.70       | 4.90  | 0.185     | 0.193 |
| A1   | 1.30       | 1.50  | 0.051     | 0.059 |
| A2   | 1.45       | 1.65  | 0.057     | 0.065 |
| b    | 0.90       | 1.15  | 0.035     | 0.045 |
| b2   | 1.90       | 2.20  | 0.075     | 0.087 |
| b4   | 2.90       | 3.20  | 0.114     | 0.126 |
| c    | 0.55       | 0.80  | 0.022     | 0.031 |
| D    | 19.80      | 20.10 | 0.780     | 0.791 |
| D1   | 16.90      | 17.20 | 0.665     | 0.677 |
| E    | 15.50      | 15.80 | 0.610     | 0.622 |
| E1   | 13.50      | 13.70 | 0.531     | 0.539 |
| e    | 5.45 BSC   |       | 0.215 BSC |       |
| L    | 19.80      | 20.20 | 0.780     | 0.795 |
| L1   | 3.40       | 3.60  | 0.134     | 0.142 |
| Ø P  | 3.20       | 3.40  | 0.126     | 0.134 |
| ØP1  | 6.90       | 7.10  | 0.272     | 0.280 |
| S    | 4.90       | 5.10  | 0.193     | 0.201 |



## Fast Diode

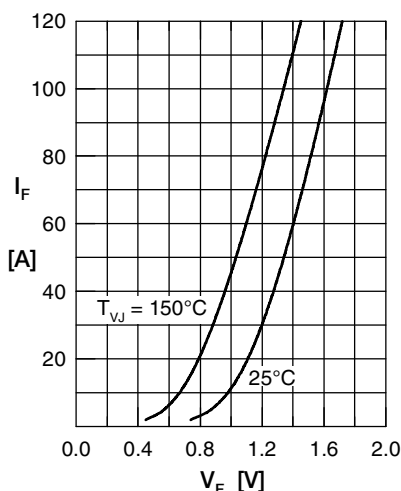


Fig. 1 Forward current  $I_F$  versus  $V_F$

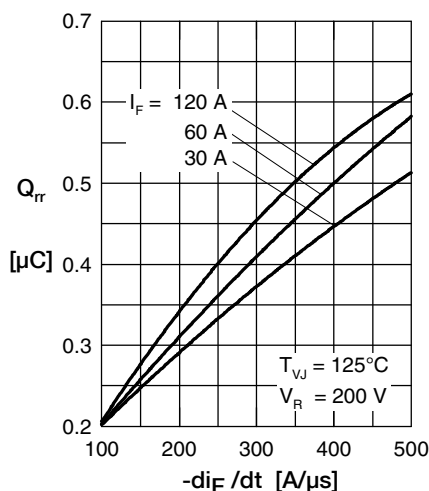


Fig. 2 Typ. reverse recov. charge  $Q_{rr}$  versus  $-di_F/dt$

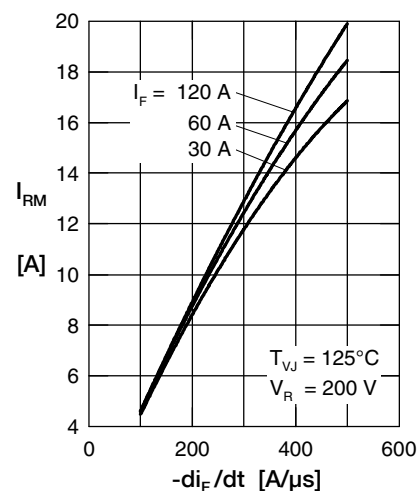


Fig. 3 Typ. reverse recov. current  $I_{RM}$  versus  $-di_F/dt$

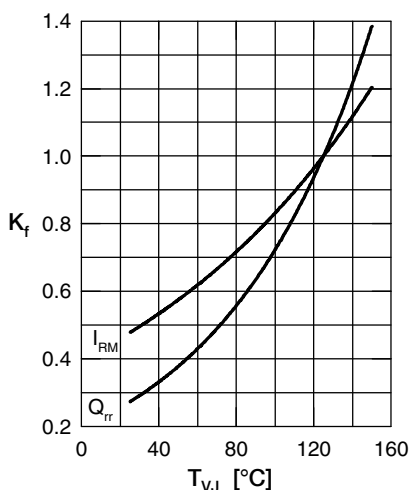


Fig. 4 Typ. dynamic parameters  $Q_{rr}$ ,  $I_{RM}$  versus  $T_{VJ}$

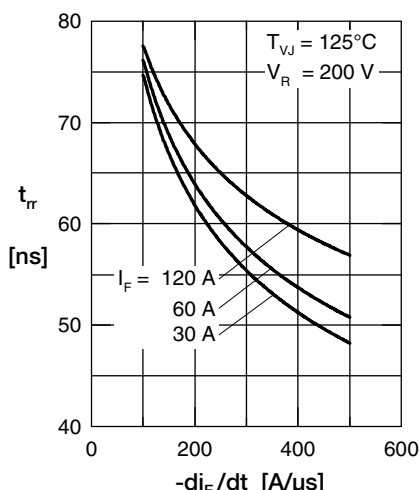


Fig. 5 Typ. reverse recov. time  $t_{rr}$  versus  $-di_F/dt$

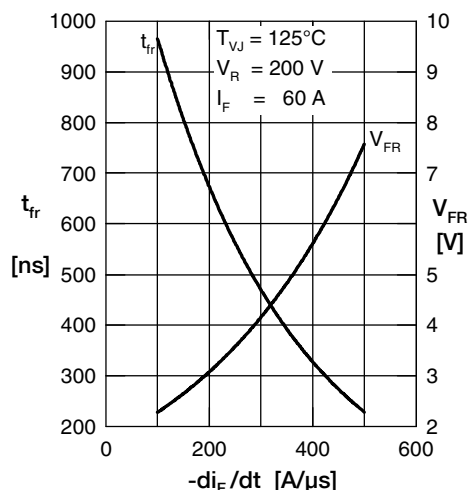


Fig. 6 Typ. forward recov. voltage  $V_{FR}$  & time  $t_{fr}$  versus  $di_F/dt$

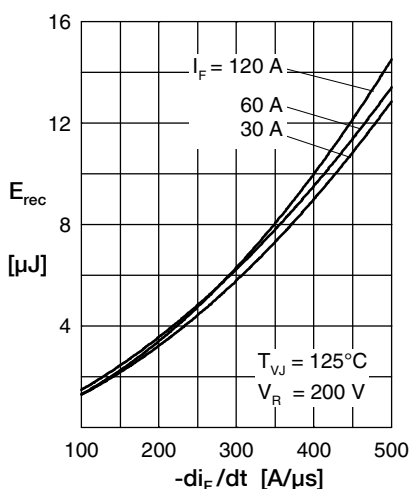


Fig. 7 Typ. recovery energy  $E_{rec}$  versus  $-di_F/dt$

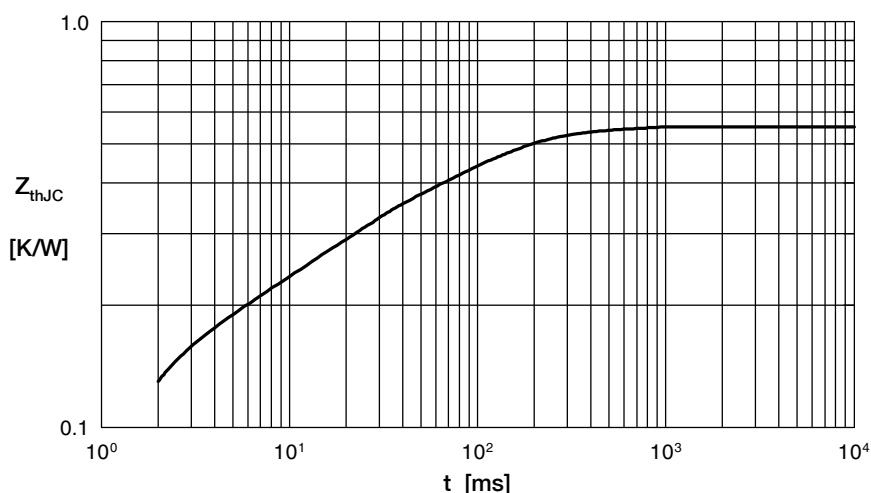


Fig. 8 Transient thermal impedance junction to case